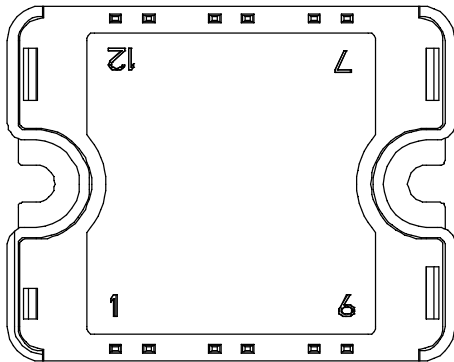
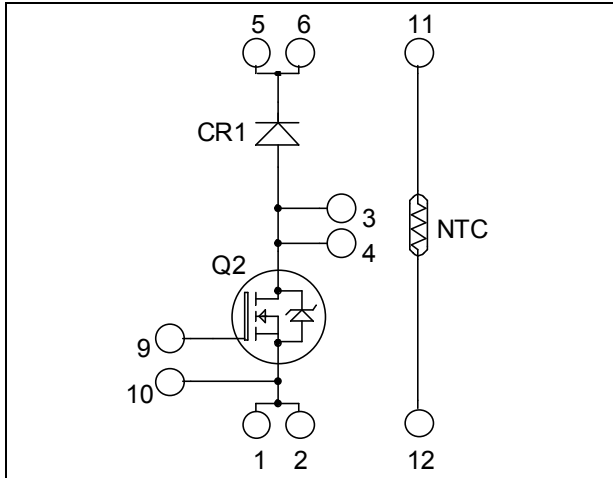


Boost chopper Super Junction MOSFET Power Module

$$V_{DSS} = 900V$$

$$R_{DSon} = 60m\Omega \text{ max @ } T_j = 25^\circ C$$

$$I_D = 59A \text{ @ } T_c = 25^\circ C$$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features



- Ultra low R_{DSon}
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated
- Very rugged
- **CRI SiC Schottky Diode**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	900	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	59
		$T_c = 80^\circ C$	44
I_{DM}	Pulsed Drain current	150	A
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	60	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	462
I_{AR}	Avalanche current (repetitive and non repetitive)	8.8	A
E_{AR}	Repetitive Avalanche Energy	2.9	mJ
E_{AS}	Single Pulse Avalanche Energy	1940	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 900V$ $T_j = 25^\circ\text{C}$			200	μA
		$V_{GS} = 0V, V_{DS} = 900V$ $T_j = 125^\circ\text{C}$		1000		
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 52A$		50	60	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 6\text{mA}$	2.5	3	3.5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V; V_{DS} = 100V$ $f = 1\text{MHz}$		13.6		nF
C_{oss}	Output Capacitance			0.66		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 52A$		540		nC
Q_{gs}	Gate – Source Charge			64		
Q_{gd}	Gate – Drain Charge			230		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GS} = 10V$ $V_{Bus} = 600V$ $I_D = 52A$ $R_G = 3.8\Omega$		70		ns
T_r	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			400		
T_f	Fall Time			25		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 10V; V_{Bus} = 600V$ $I_D = 52A; R_G = 3.8\Omega$		1.8		mJ
E_{off}	Turn-off Switching Energy			1.5		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 10V; V_{Bus} = 600V$ $I_D = 52A; R_G = 3.8\Omega$		2.52		mJ
E_{off}	Turn-off Switching Energy			1.7		

CR1 SiC diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$	96	600	μA
			$T_j = 175^\circ\text{C}$	168	3000	
I_F	DC Forward Current			30		A
V_F	Diode Forward Voltage	$I_F = 30A$	$T_j = 25^\circ\text{C}$	1.6	1.8	V
			$T_j = 175^\circ\text{C}$	2.3	3	
Q_C	Total Capacitive Charge	$I_F = 30A, V_R = 600V$ $di/dt = 1000A/\mu\text{s}$		120		nC
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200V$		288		pF
		$f = 1\text{MHz}, V_R = 400V$		207		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	CoolMOS		0.27	°C/W	
		SiC Diode		0.63		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

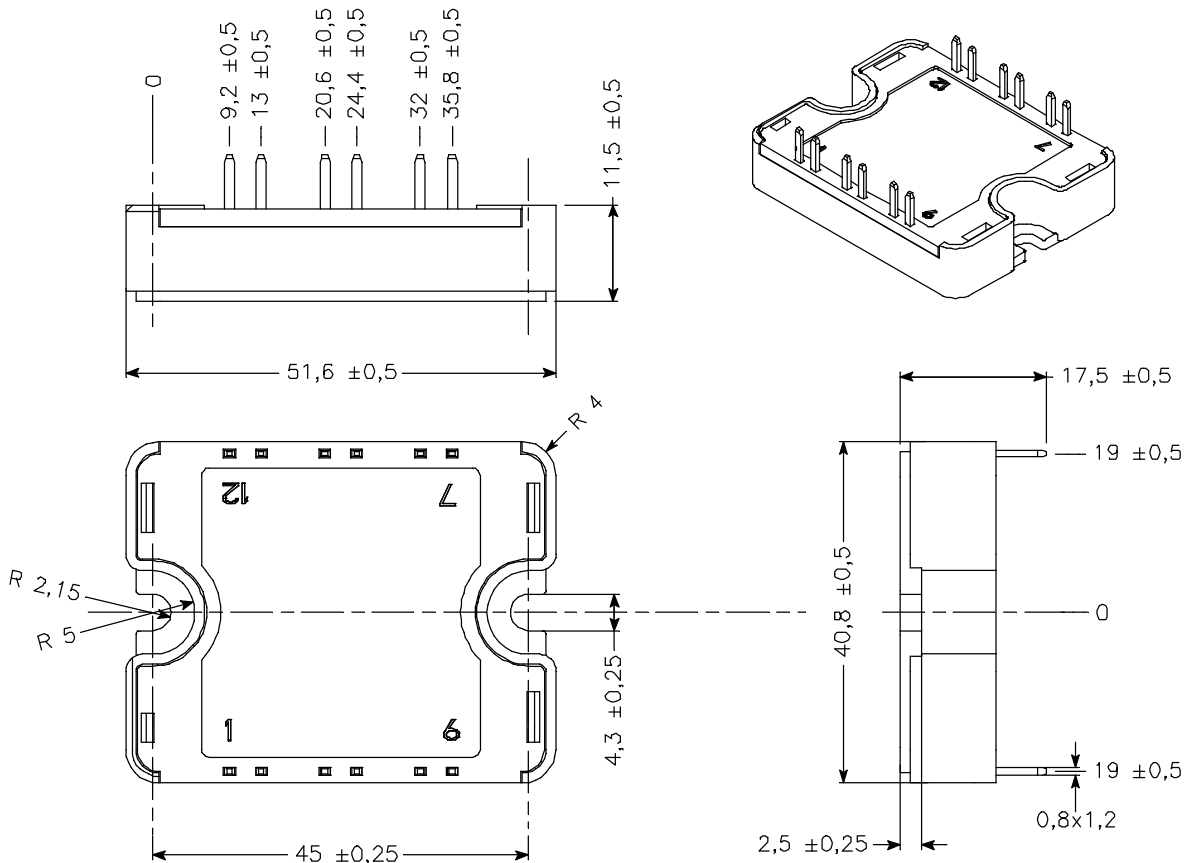
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

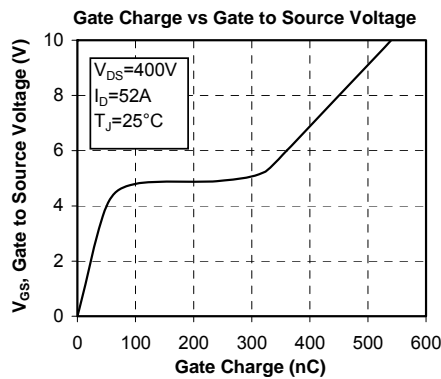
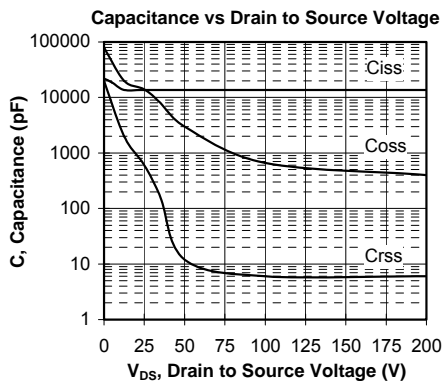
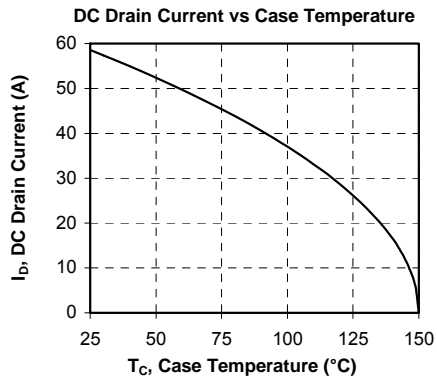
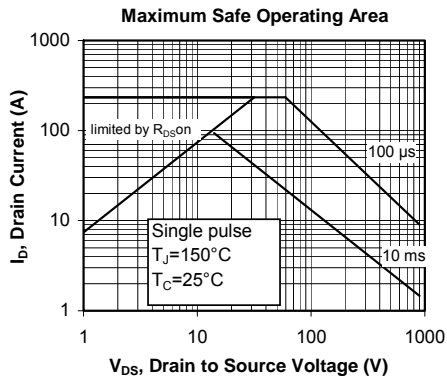
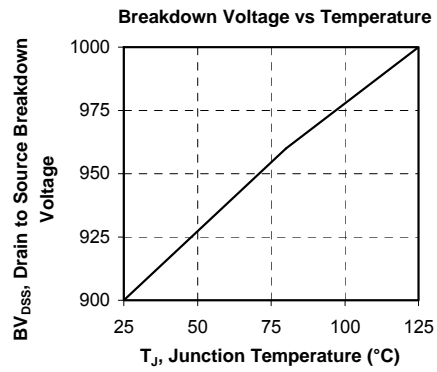
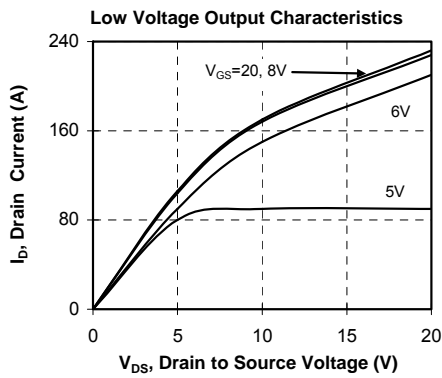
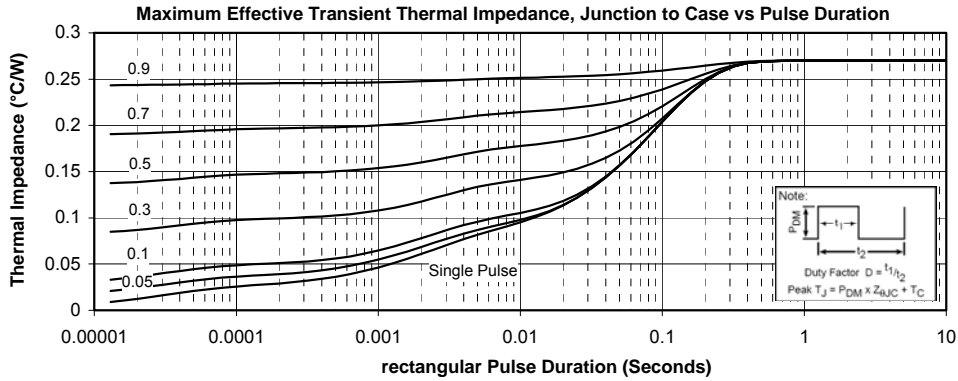
T: Thermistor temperature
 R_T: Thermistor value at T

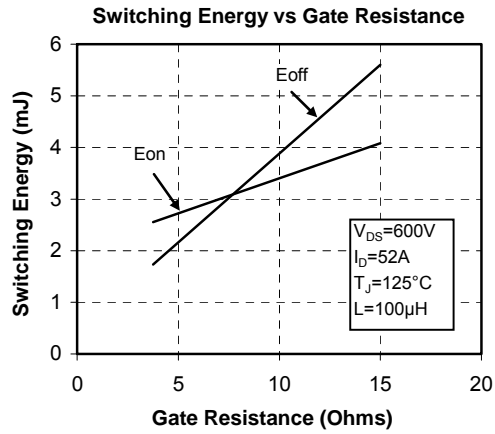
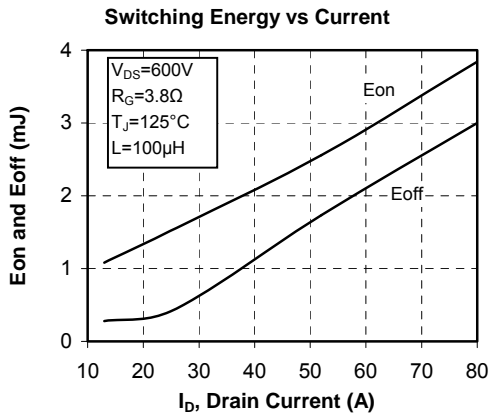
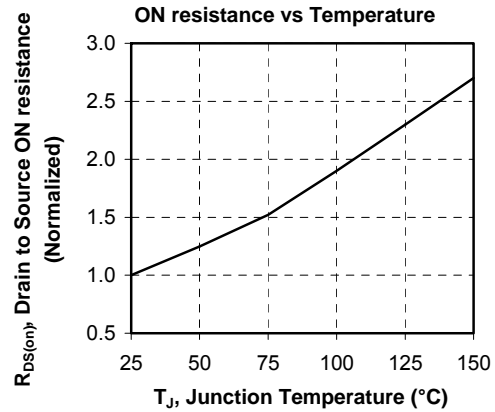
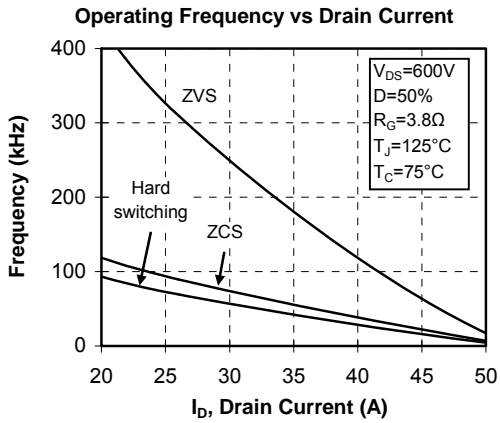
SP1 Package outline (dimensions in mm)



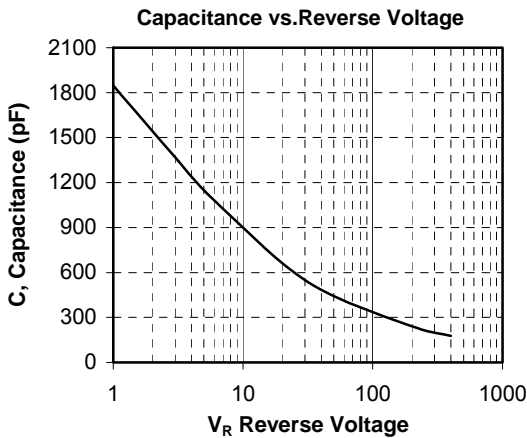
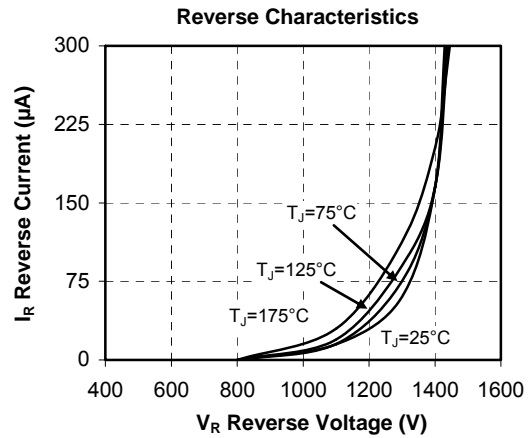
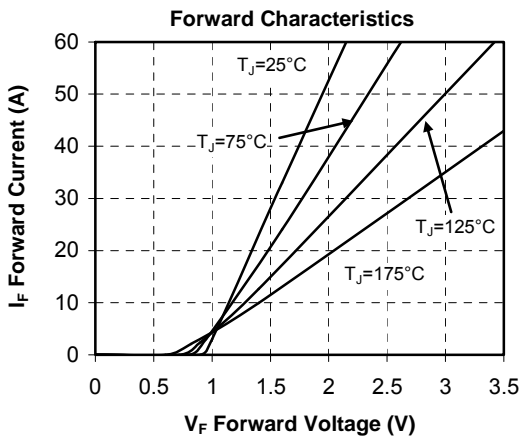
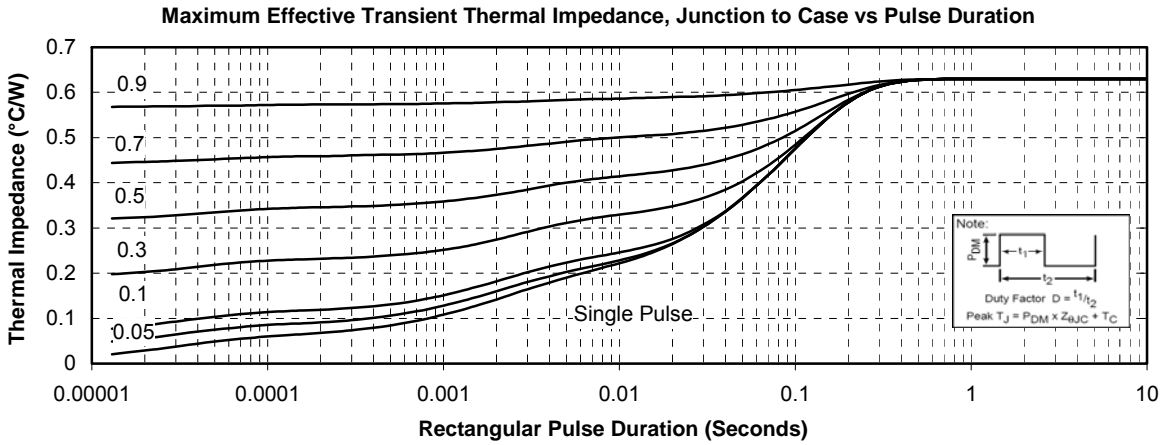
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Typical CoolMOS Performance Curve





Typical CR1 SiC Diode Performance Curve



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